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- High efficiency
- High current capability
- High Reliability
- High surge current capability
- Glass passivated chip junction
- Solder dip 275 °C max. 7 s, per JESD 22-B106

- : R-1
- Molding 11455

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	FSM	A	30		
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25			60		
Current squared time @1ms≤t≤8.3ms Tj=25 Rating of per diode	I ² t	A ² s	3.735		
Typical junction capacitance @ Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	Cj	pF	15	13	8
Storage Temperature	Tstg		-55 ~ +150		
Junction Temperature	Tj		-55 ~ +150		

■ Ta=25 Unless otherwise specified

Maximum instantaneous forward voltage drop per diode	VF	V	IFM=1.0A	1.0	1.3	1.7				

Maximum DC reverse current at rated DC blocking voltage per diode

IR μA

Tj=25

v7KHUPDO &KDUDÄFVHULVWLFV

- D Q



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